



**ELECTRONICS, INC.**  
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## NTE56045 thru NTE56047 TRIAC, 16A, Sensitive Gate

### **Description:**

The NTE56045 through NTE56047 are glass passivated, sensitive gate TRIACs in an isolated full-pack type package designed for use in general purpose bidirectional switching and phase control applications, where high sensitivity is required in all four quadrants.

### **Absolute Maximum Ratings:**

Repetitive Peak Off-State Voltage, $V_{DRM}$	
NTE56045 (Note 1) .....	500V
NTE56046 (Note 1) .....	600V
NTE56047 .....	800V
RMS On-State Current (Full Sine Wave, $T_{HS} \leq 38^{\circ}C$ ), $I_T(RMS)$ .....	16A
Non-Repetitive Peak On-State Current, $I_{TSM}$	
(Full Sine Wave, $T_J = +125^{\circ}C$ prior to Surge, with Reapplied $V_{DRMmax}$ )	
$t = 20ms$ .....	140A
$t = 16.7ms$ .....	150A
$I^2t$ for Fusing ( $t = 10ms$ ), $I^2t$ .....	98A <sup>2</sup> sec
Repetitive Rate-of-Rise of On-State Current after Triggering, $di_T/dt$	
( $I_{TM} = 20A$ , $I_G = 0.2A$ , $di_G/dt = 0.2A/\mu s$ )	
$MT_2 (+)$ , $G (+)$ .....	50A/ $\mu s$
$MT_2 (+)$ , $G (-)$ .....	50A/ $\mu s$
$MT_2 (-)$ , $G (-)$ .....	50A/ $\mu s$
$MT_2 (-)$ , $G (+)$ .....	10A/ $\mu s$
Peak Gate Current, $I_{GM}$ .....	2A
Peak Gate Voltage, $V_{GM}$ .....	5V
Peak Gate Power, $P_{GM}$ .....	5W
Average Gate Power (Over Any 20ms Period), $P_{G(AV)}$ .....	500mW
Operating Junction Temperature, $T_J$ .....	+125°C
Storage Temperature Range, $T_{stg}$ .....	-40° to +150°C
Thermal Resistance, Junction-to-Heatsink (Full or Half Cycle), $R_{thJHS}$	
With Heatsink Compound .....	4.0K/W
Without Heatsink Compound .....	5.5K/W
Typical Thermal Resistance, Junction-to-Ambient, $R_{thJA}$ .....	55K/W

Note 1. Although not recommended, off-state voltages up to 800V may be applied without damage, but the TRIAC may switch to the on-state. The rate-of-rise of current should not exceed 15A/ $\mu s$ .

**Electrical Characteristics:** ( $T_J = +25^\circ\text{C}$  unless otherwise specified)

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Gate Trigger Current MT <sub>2</sub> (+), G (+)	I <sub>GT</sub>	V <sub>D</sub> = 12V, I <sub>T</sub> = 0.1A	–	2.5	10	mA
MT <sub>2</sub> (+), G (–)			–	4.0	10	mA
MT <sub>2</sub> (–), G (–)			–	5.0	10	mA
MT <sub>2</sub> (–), G (+)			–	11	25	mA
Latching Current MT <sub>2</sub> (+), G (+)	I <sub>L</sub>	V <sub>D</sub> = 12V, I <sub>T</sub> = 0.1A	–	3.2	30	mA
MT <sub>2</sub> (+), G (–)			–	16	40	mA
MT <sub>2</sub> (–), G (–)			–	4.0	30	mA
MT <sub>2</sub> (–), G (+)			–	5.5	40	mA
Holding Current	I <sub>H</sub>	V <sub>D</sub> = 12V, I <sub>T</sub> = 0.1A	–	4.0	30	mA
On–State Voltage	V <sub>T</sub>	I <sub>T</sub> = 20A	–	1.2	1.6	V
Gate Trigger Voltage	V <sub>GT</sub>	V <sub>D</sub> = 12V, I <sub>T</sub> = 0.1A	–	0.7	1.5	V
		V <sub>D</sub> = 400V, I <sub>T</sub> = 0.1A, T <sub>J</sub> = +125°C	0.25	0.4	–	V
Off–State Leakage Current	I <sub>D</sub>	V <sub>D</sub> = V <sub>DRM</sub> max, T <sub>J</sub> = +125°C	–	0.1	0.5	mA
<b>Dynamic Characteristics</b>						
Critical Rate–of–Rise of Off–State Voltage	dV <sub>D</sub> /dt	V <sub>DM</sub> = 67% V <sub>DRM</sub> max, T <sub>J</sub> = +125°C, Exponential Waveform, Gate Open	–	50	–	V/μs
Gate Controlled Turn–On Time	t <sub>gt</sub>	I <sub>TM</sub> = 20A, V <sub>D</sub> = V <sub>DRM</sub> max, I <sub>G</sub> = 0.1A, dI <sub>G</sub> /dt = 5A/μs	–	2	–	μs
<b>Isolation Characteristics</b> (T <sub>hs</sub> = +25°C unless otherwise specified)						
RMS Isolation Voltage from All 3 Pins to External Heatsink	V <sub>ISOL</sub>	f = 50 – 60Hz, Sinusoidal Waveform, R.H. ≤ 65%, Clean and Dustfree	–	–	2500	V
Capacitance from T2 to External Heatsink	C <sub>ISOL</sub>	f = 1MHz	–	10	–	pF

